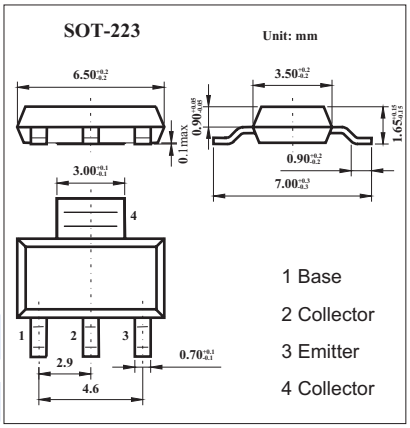
2.0W Surface Mount Complementary NPN Silicon Power Transistor KZT3055(CZT3055)

Features

- High current (max. 6A).
- Low voltage (max. 60V).



Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	100	V
Collector - emitter votage	V_{CER}	70	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	7	V
Collector current	I_C	6	A
Base current	I_B	3	A
power dissipation	P_D	2	W
Thermal resistance Junction-to-Ambient	$R_{\theta JA}$	62.5	℃/W
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-65 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector to emitter breakdown voltage	V_{CEO}	I_C=30mA	60			V
Collector to emitter breakdown voltage	V_{CER}	I_C=30mA,R_{BE}=100 Ω	70			V
Collctor cutoff current	I_{CEO}	V_{CE}=30V			700	μ A
	I_{CEV}	V_{CE}=100V,V_{EB}=1.5V			1.0	mA
Emitter cutoff current	I_{EBO}	V_{EB} = 7.0 V			5.0	m A
DC current gain	h_{FE}	I_C = 4.0A; V_{CE} =4.0 V	20		70	
		I_C = 6.0A; V_{CE} = 4.0V	5.0			
Collector to emitter saturation voltage	$V_{CE(sat)}$	I_C = 4.0A; I_B =400mA			1.1	V
Base to emitter ON voltage	$V_{BE(on)}$	V_{CE}=4.0V,I_C=4.0A			1.5	V
Transition frequency	f_T	I_C= 500mA; V_{CE} =10V; f = 1.0 MHz	2.5			MHz